



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	1.6m Ω @10V	280A

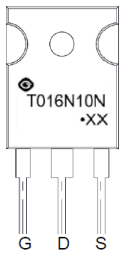
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

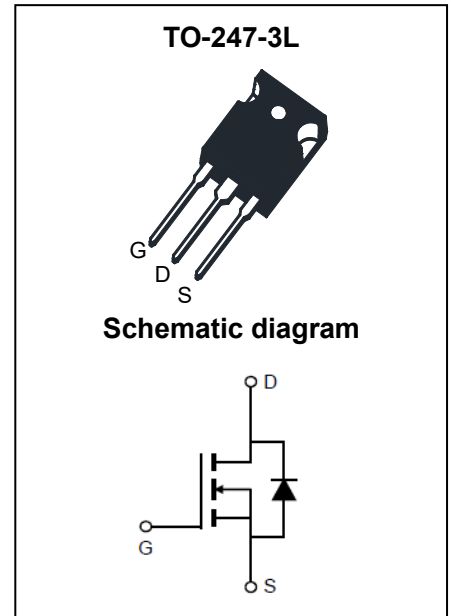
Application

- Power Switching Application

MARKING:



T016N10N = Device Code
XX = Date Code
Solid Dot = Green Indicator



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	100	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	280 A
	$T_C = 100^\circ\text{C}$	I_D	182 A
Pulsed Drain Current ²	I_{DM}	1120	A
Single Pulsed Avalanche Current ³	I_{AS}	90	A
Single Pulsed Avalanche Energy ³	E_{AS}	2300	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	347 W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	40	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.36	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

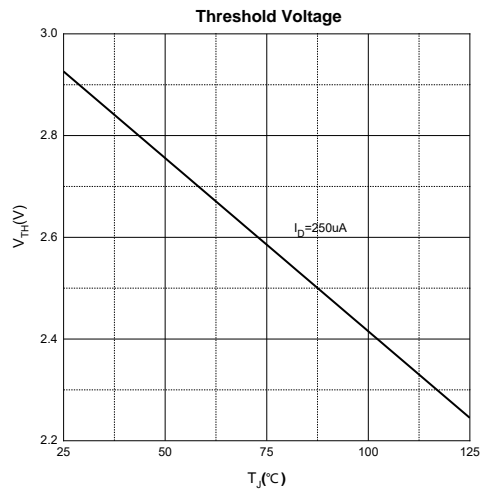
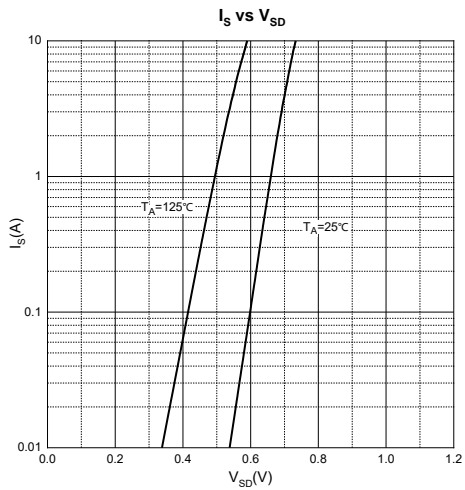
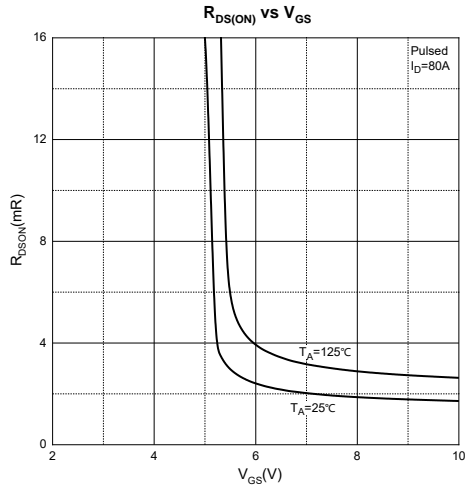
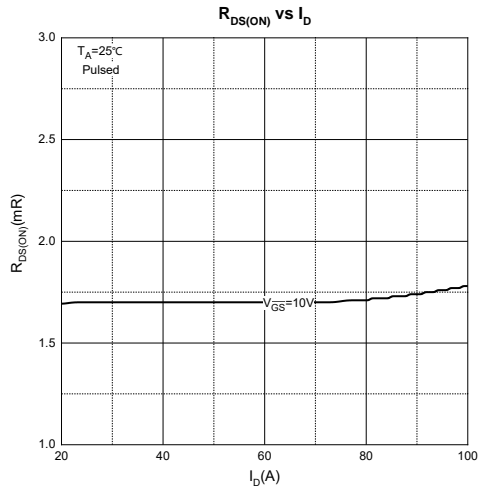
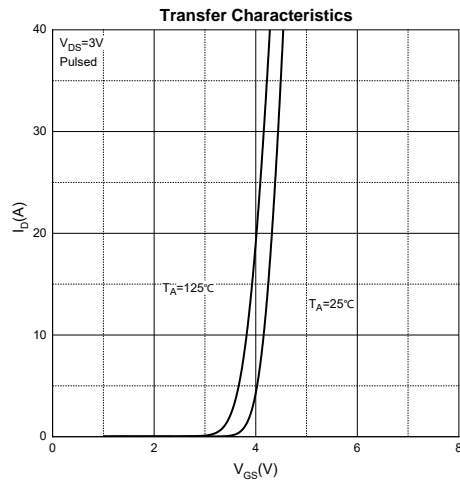
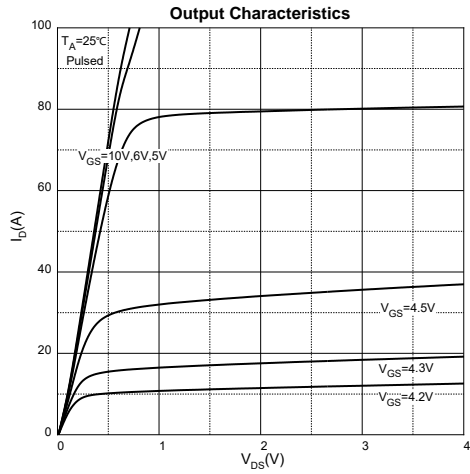
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

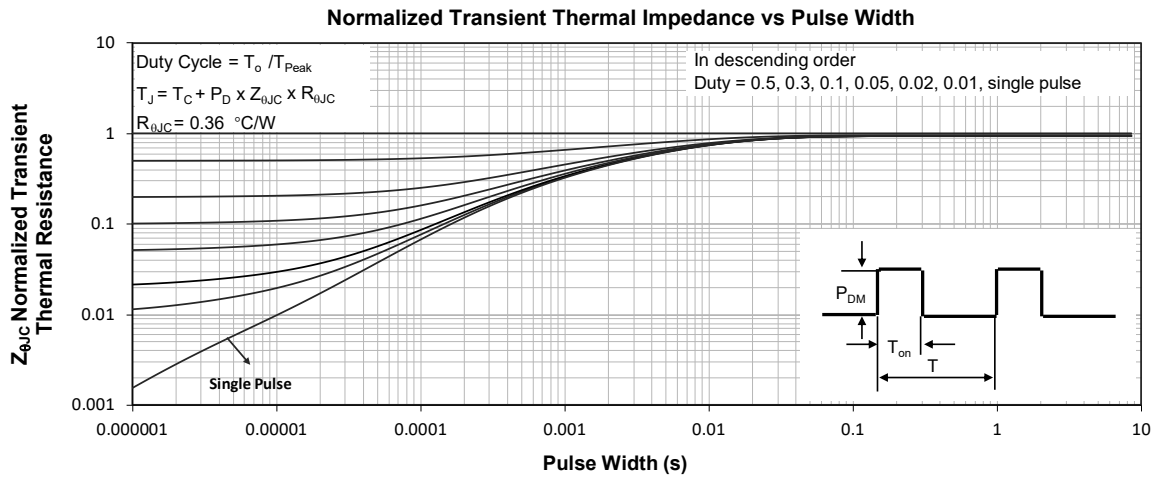
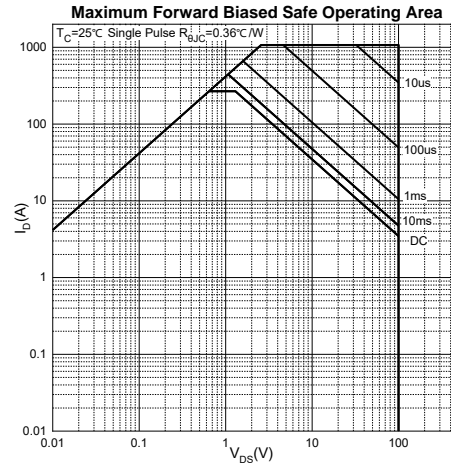
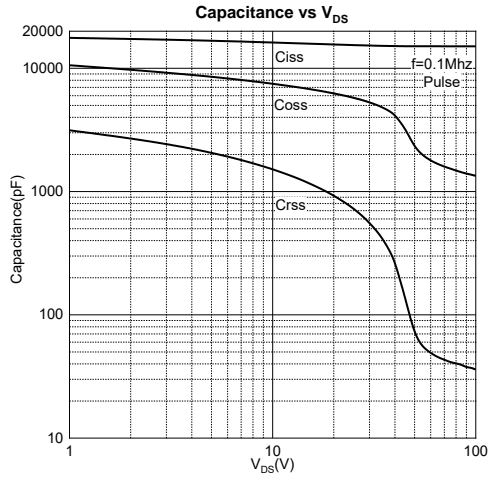
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		1.6	2	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 0.1MHz$		15106		pF
Output Capacitance	C_{oss}			2280		
Reverse Transfer Capacitance	C_{rss}			69		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		3		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 20A$		250.2		nC
Gate-source Charge	Q_{gs}			61.4		
Gate-drain Charge	Q_{gd}			68		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, I_D = 20A, R_G = 3\Omega$		40		ns
Turn-on Rise Time	t_r			90		
Turn-off Delay Time	$t_{d(off)}$			160		
Turn-off Fall Time	t_f			100		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 10A$			1.2	V

Notes :

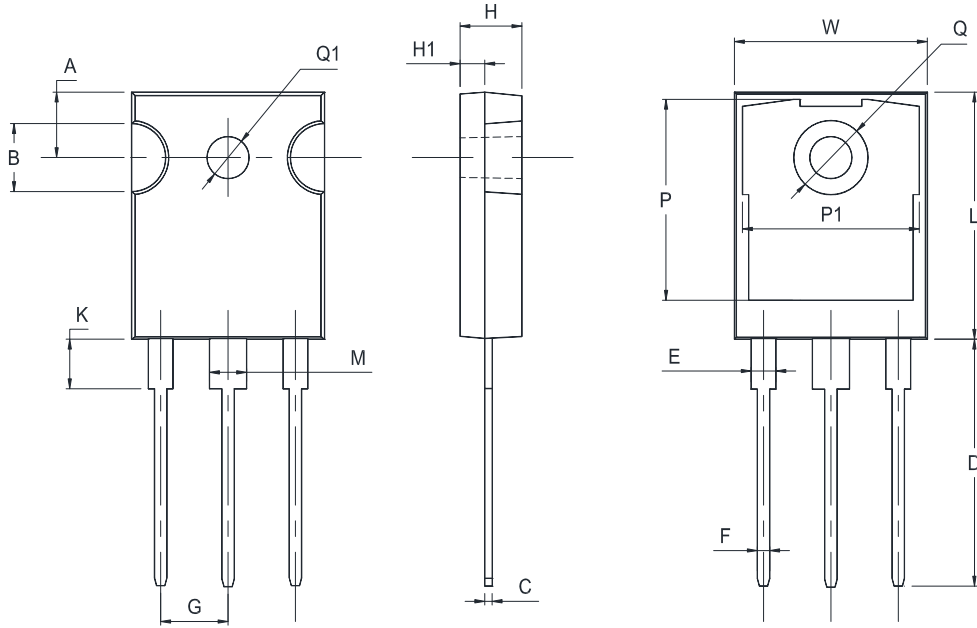
1. The maximum current rating is limited by package. And device mounted on a large heatsink
2. Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
3. E_{AS} condition: $V_{DD} = 50V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$. And device mounted on a large heatsink
6. Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics





TO-247-3L Package Information



UNIT	A	B	C	D	E	F	G	W	H	H1	K	L	M	P
mm	6.5	5.2	0.7	20.3	2.2	1.3	5.7	16.2	5.3	2.5	4.45	21.3	3.2	16.6
	5.9	4.6	0.5	19.7	1.8	1.1	5.1	15.8	4.7	2.1	4.05	20.7	2.8	16.2

UNIT	P1	Q	Q1
mm	14.2	7.35	4.2
	13.8	7.05	3.6

